

DESCRIPTION

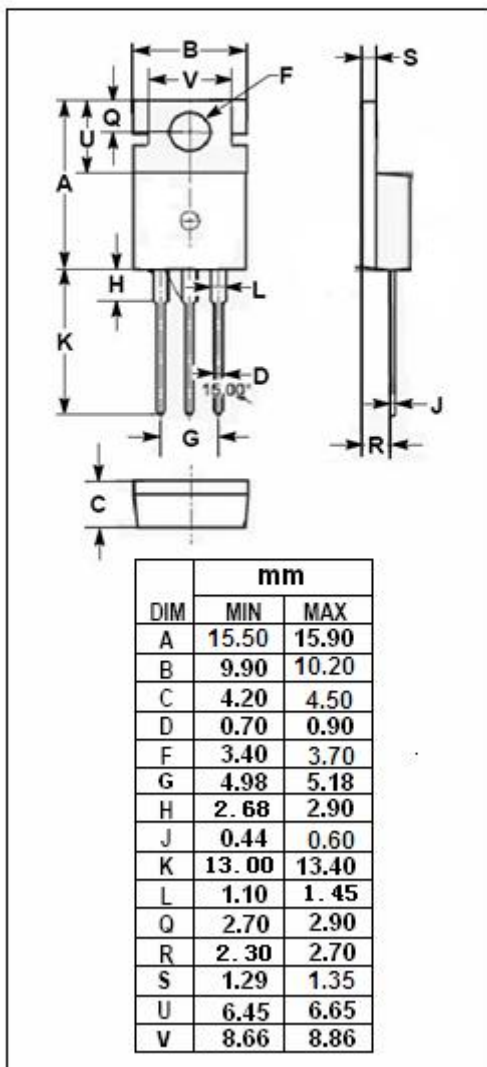
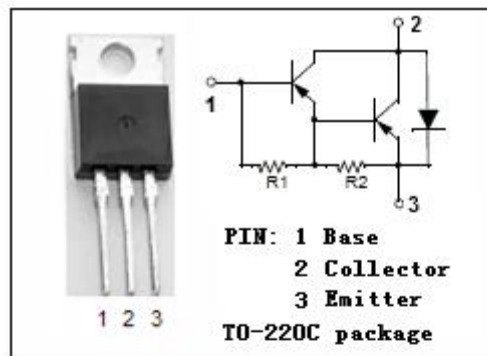
- High DC Current Gain-
: $h_{FE} = 1000(\text{Min}) @ I_C = -3A$
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -120V(\text{Min})$
- Low Collector-Emitter Saturation Voltage-
: $V_{CE(sat)} = -1.5V(\text{Max}) @ I_C = -3A$
- Complement to Type 2SD768

APPLICATIONS

- Medium speed and power switching applications.

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-120	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current-Continuous	-6	A
I_{CM}	Collector Current-Peak	-10	A
P_C	Collector Power Dissipation $T_C = 25^\circ\text{C}$	40	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS**T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -25mA, R _{BE} = ∞	-120			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -50mA, I _C = 0	-7			V
V _{CE(sat)-1★}	Collector-Emitter Saturation Voltage	I _C = -3A, I _B = -6mA			-1.5	V
V _{CE(sat)-2★}	Collector-Emitter Saturation Voltage	I _C = -6A, I _B = -60mA			-3.0	V
V _{BE(sat)-1★}	Base-Emitter Saturation Voltage	I _C = -3A, I _B = -6mA			-2.0	V
V _{BE(sat)-2★}	Base-Emitter Saturation Voltage	I _C = -6A, I _B = -60mA			-3.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -120V, I _E = 0			-100	μ A
I _{CEO}	Collector Cutoff Current	V _{CE} = -100V; R _{BE} = ∞			-10	μ A
h _{FE★}	DC Current Gain	I _C = -3A; V _{CE} = -3V	1000		20000	

★:Pulse Test